

REMARKS

Claims 1-37 are in the application. Claims 1, 2, 11, 24, 31, and 34 are in independent form.

FIGS. 3 and 4 are replaced with new FIGS. 3 and 4 that include positioning mirror 44, which was inadvertently omitted/mislabeled in the original FIGS. 3 and 4. Positioning mirror 44 is mentioned in the Detailed Description of Preferred Embodiments. Applicants believe that no new matter has been added. Applicants enclose copies of the drawings with the changes shown in red ink, in addition to the replacement drawings.

Paragraph #0001 has been amended to agree with the priority claims made in the Combined Declaration and Power of Attorney form.

Paragraph #0013 has been amended to correct the spelling of the word "silicon."

Paragraph #0043 has been amended to correct a figure number (52) of the power controller to be in agreement with the drawings and the rest of the description.

Applicants present claims 1-37 for examination.

Respectfully submitted,
Brian W. Baird, Michael J. Wolfe,
Richard S. Harris, Kevin P. Fahey,
Lian-Cheng Zou, and Thomas R. McNeil

By


Michael L. Levine
Registration No. 33,947

STOEL RIVES LLP
900 SW Fifth Avenue, Suite 2600
Portland, Oregon 97204-1268
Telephone: (503) 224-3380
Facsimile: (503) 220-2480
Attorney Docket No.: 50001/83:2 USA

Version with Markings to Show Changes Made

Specification paragraph #0001 on application page 1 is amended as follows:

-- This patent application derives priority from U.S. Provisional Application No. 60/265,556, filed January 31, 2001, from U.S. Provisional Application No. 60/297,218, filed June 8, 2001, from U.S. Patent Application No. 09/957,633, filed September 19, 2001, which claims priority from U.S. Provisional Application No. 60/233,914, filed September 20, 2000, and from U.S. Patent Application No. 09/803,382, filed March 9, 2001, which claims priority from U.S. Provisional Application No. 60/233,913, filed September 20, 2000 --

Specification paragraph #0013 on application page 4 is amended as follows:

-- An object of the invention is to provide an improved method for using a laser to create microfeatures in semiconductors, including silicon, gallium arsenide (GaAs), [silcon] silicon carbide (SiC), silicon nitride (SiN), and/or Ge:Si, and/or also including such semiconductors subsequently treated in semiconductor processes, including but not limited to photolithography and etching, well known to those skilled in the art to contain additional layers for the purpose of creating useful electronic and optoelectronic circuits on semiconductor substrates, including semiconductor wafers.--

Specification paragraph #0043 on application page 9 is amended as follows:

-- An optional laser power controller 52, such as a half wave plate polarizer, may be positioned along optical path 20. In addition, one or more beam detection devices 54, such as photodiodes, may be downstream of laser power controller 52, such as aligned with a positioning mirror 44 that is adapted to be partly transmissive to the wavelength of laser output 16. Beam detection devices 54 are preferably in communication with beam diagnostic electronics that convey signals to modify the effects of laser power controller [54] 52. --